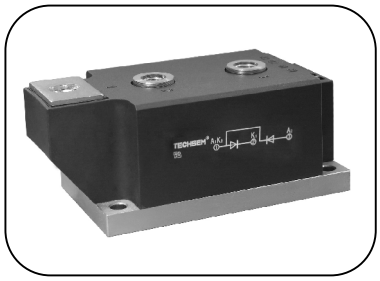


Features：

- **n** Isolated mounting base 4000V~
- **n** Pressure contact technology with Increased power cycling capability
- **n** Space and weight saving

Typical Applications

- **n** Various rectifiers
- **n** DC supply for PWM inverter

V_{RRM}	Type & Outline
2600V	MDx350-26-415F3
2800V	MDx350-28-415F3
3000V	MDx350-30-415F3
3200V	MDx350-32-415F3
3400V	MDx350-34-415F3
3600V	MDx350-36-415F3
3600V	MD350-36-415F3G

MDx stands for any type of **MDC, MDA, MDK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			350	A
$I_{F(RMS)}$	RMS forward current					550	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			35	mA
I_{FSM}	Surge forward current	V_R=60%V_{RRM}, t=10ms half sine	150			11	kA
I^2t	I^2t for fusing coordination					605	10^3A^2s
V_{FO}	Threshold voltage		150			0.87	V
r_F	Forward slope resistance					0.50	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1050A	25			1.75	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.11	°C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.04	°C/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(MAX)		4000			V
F_m	Terminal connection torque(M10)			10		12	N·m
	Mounting torque(M6)			4.5		6.0	N·m
T_{vj}	Junction temperature			-40		150	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				1260		g
Outline	415F3						

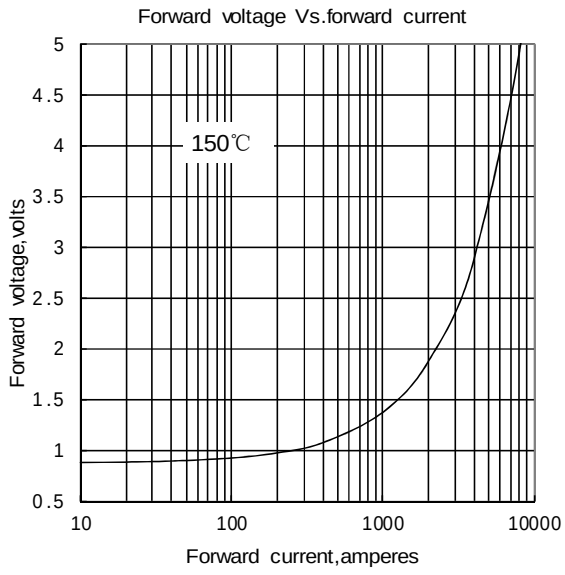


Fig.1

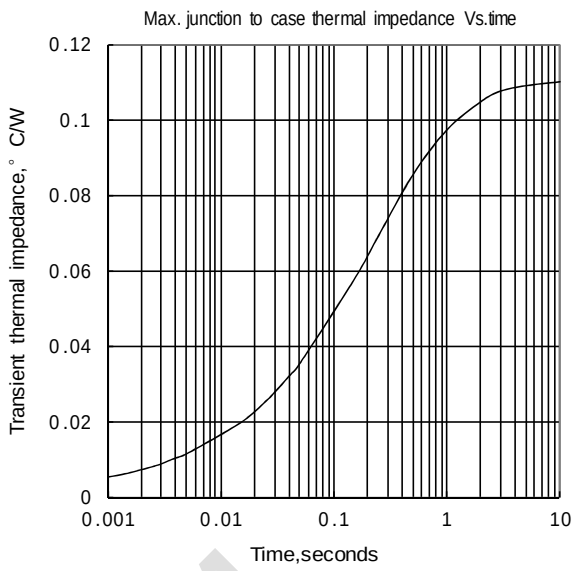


Fig.2

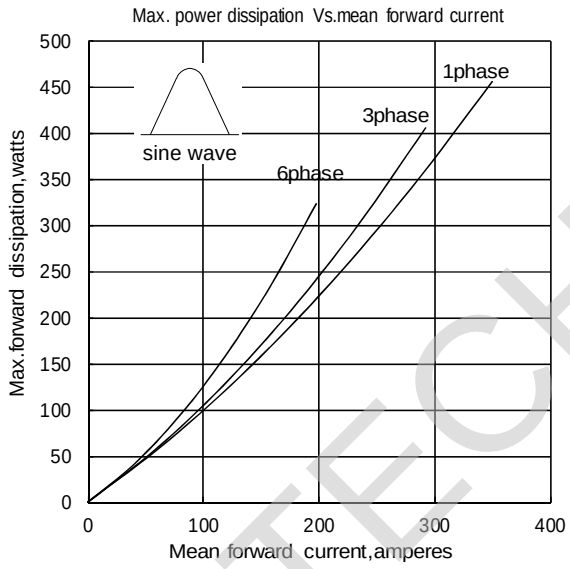


Fig.3

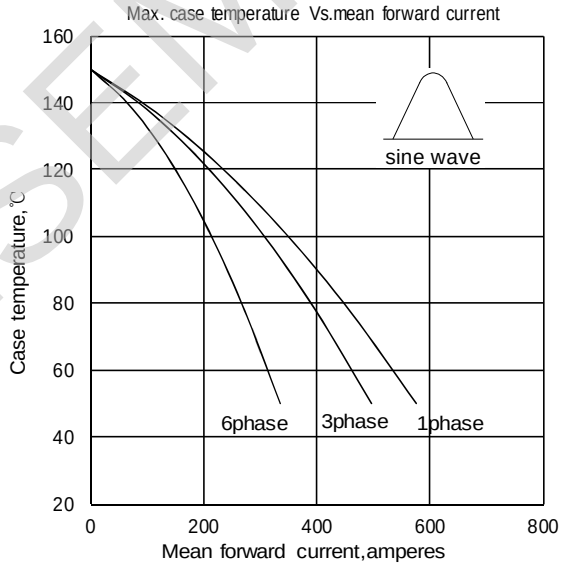


Fig.4

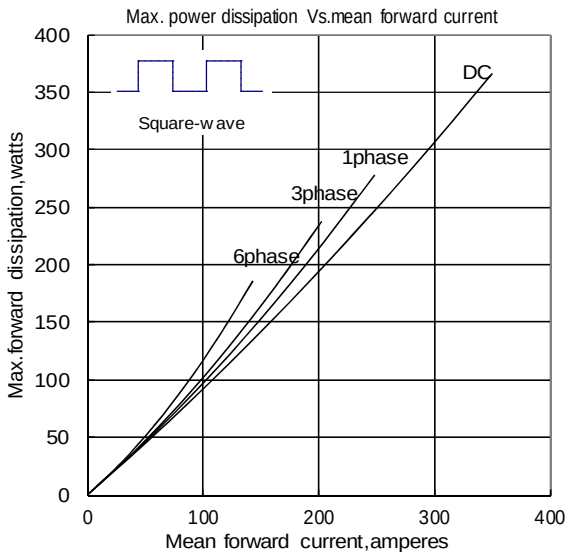


Fig.5

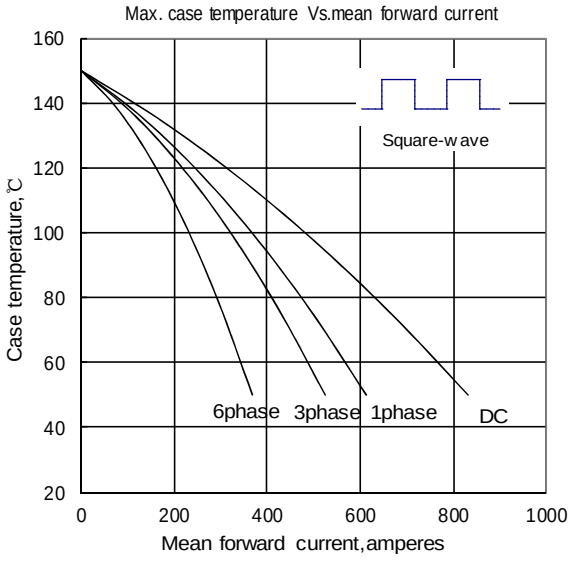


Fig.6

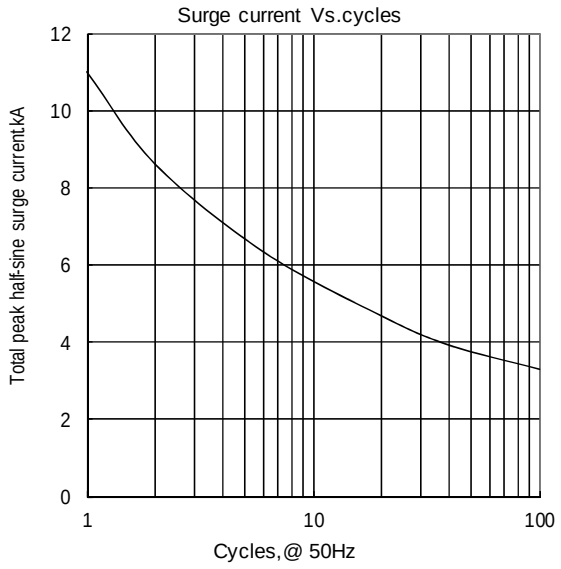


Fig.7

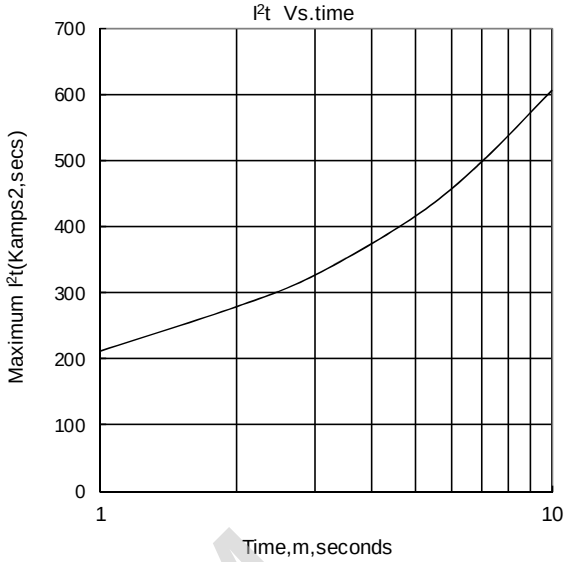
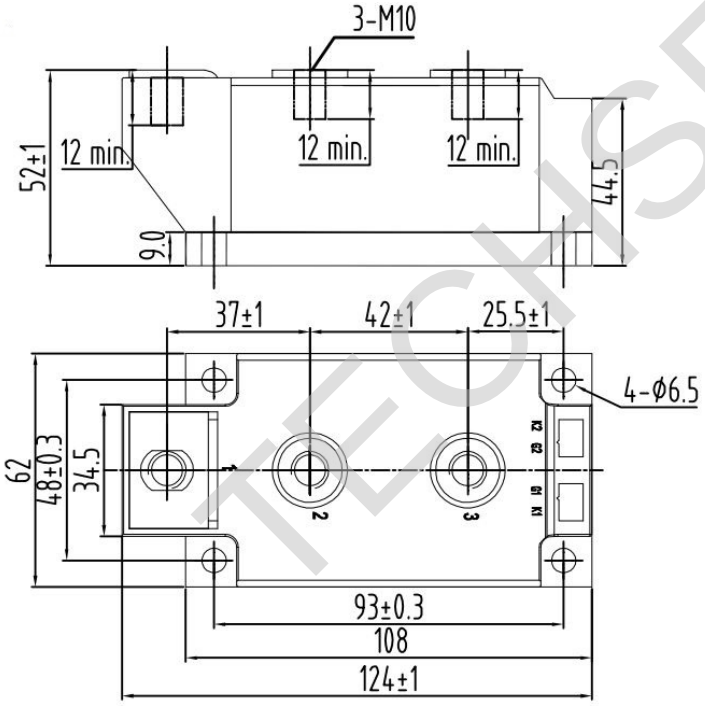
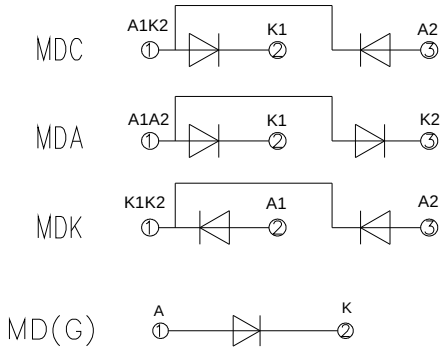


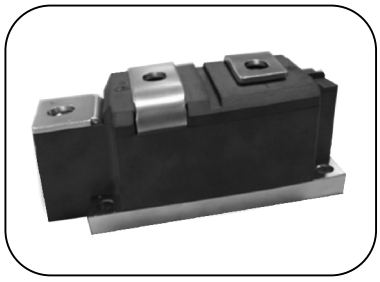
Fig.8

Outline:





Unmarked dimensional tolerance：±0.5mm



Features：

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- Pressure contact technology with Increased power cycling capability
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Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{RRM}	Type & Outline
2600V	MDx500-26-410F3
2800V	MDx500-28-410F3
3000V	MDx500-30-410F3
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3400V	MDx500-34-410F3
3600V	MDx500-36-410F3
3600V	MD500-36-410F3G

MDx stands for any type of **MDC, MDA, MDK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			500	A
$I_{F(RMS)}$	RMS forward current					785	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			50	mA
I_{FSM}	Surge forward current	V_R=60%V_{RRM}, t=10ms half sine	150			15	kA
I^2t	I^2t for fusing coordination					1125	10^3A^2s
V_{FO}	Threshold voltage		150			0.85	V
r_F	Forward slope resistance					0.50	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1500A	25			1.85	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.060	°C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.024	°C/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(MAX)		4000			V
F_m	Terminal connection torque(M12)			12		16	N·m
	Mounting torque(M8)			10		12	N·m
T_{vj}	Junction temperature			-40		150	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				3310		g
Outline	410F3						

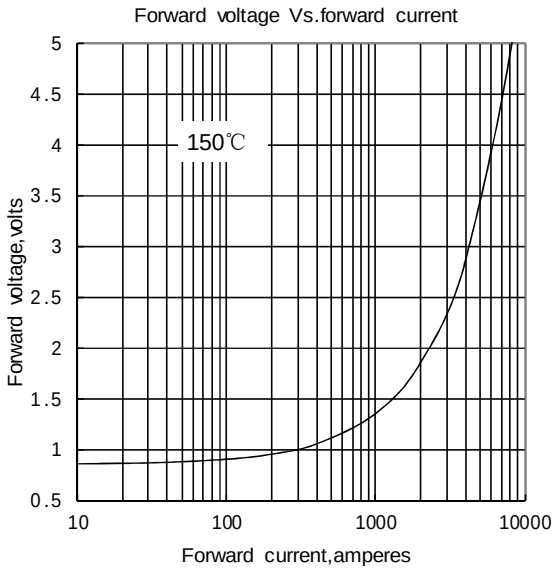


Fig.1

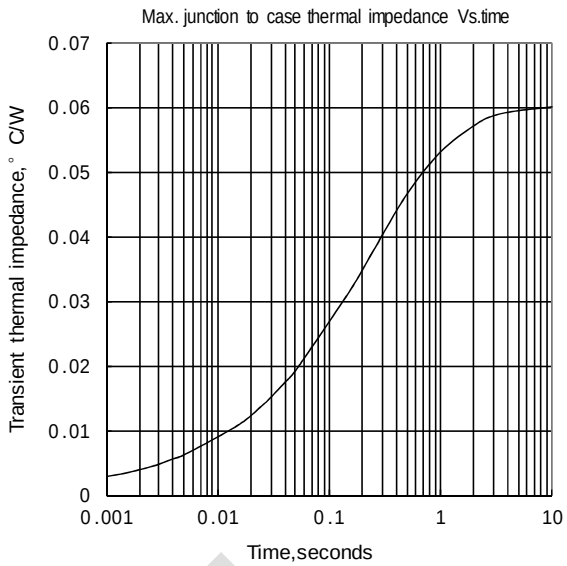


Fig.2

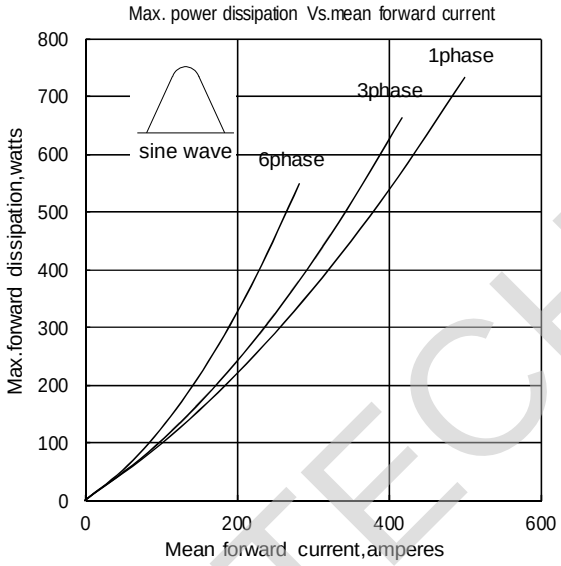


Fig.3

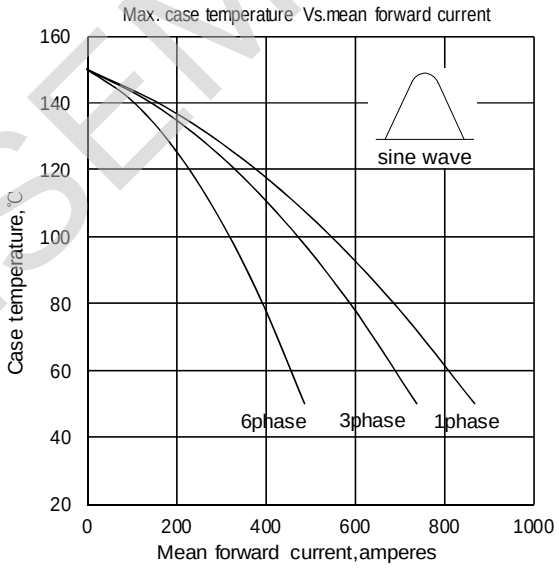


Fig.4

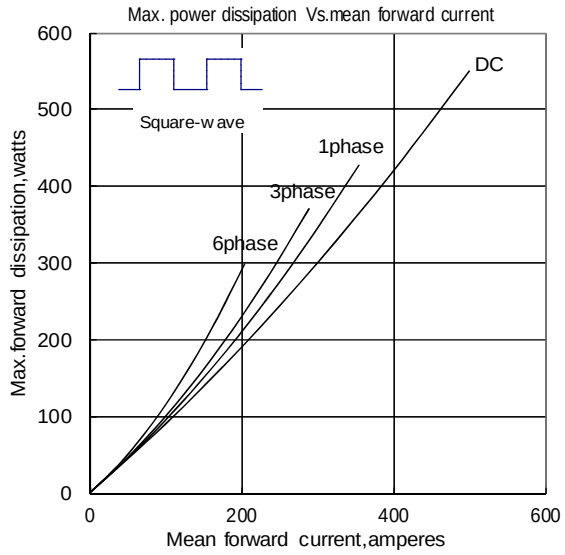


Fig.5

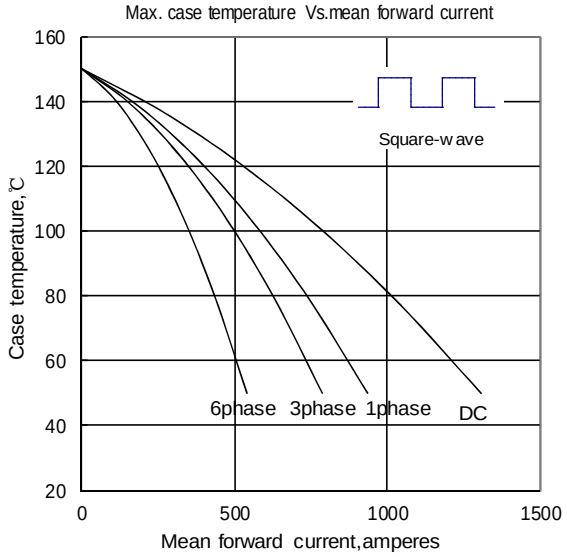


Fig.6

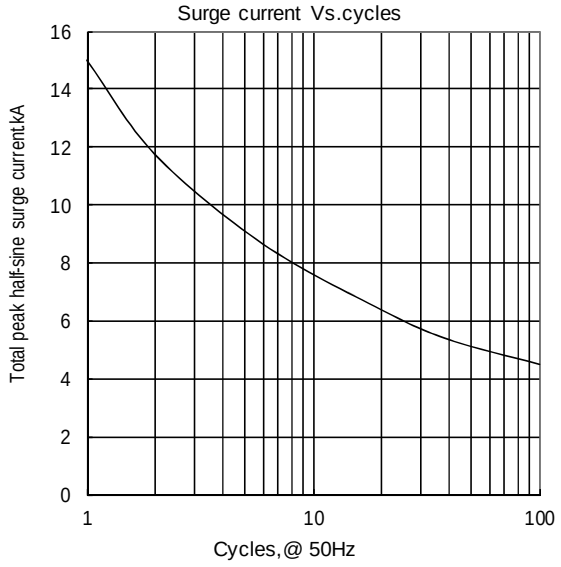


Fig.7

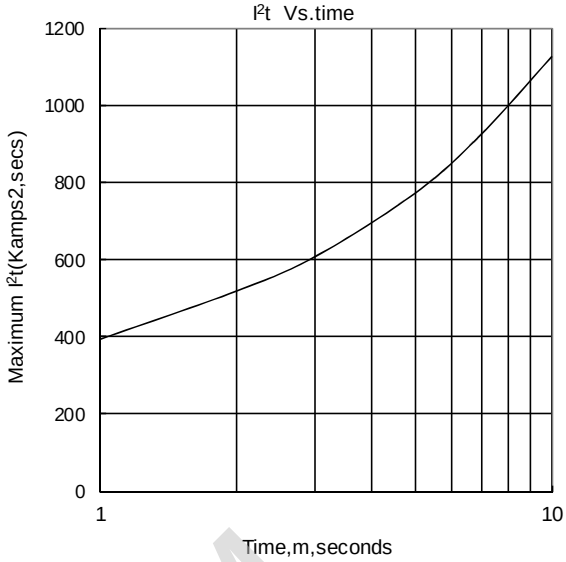
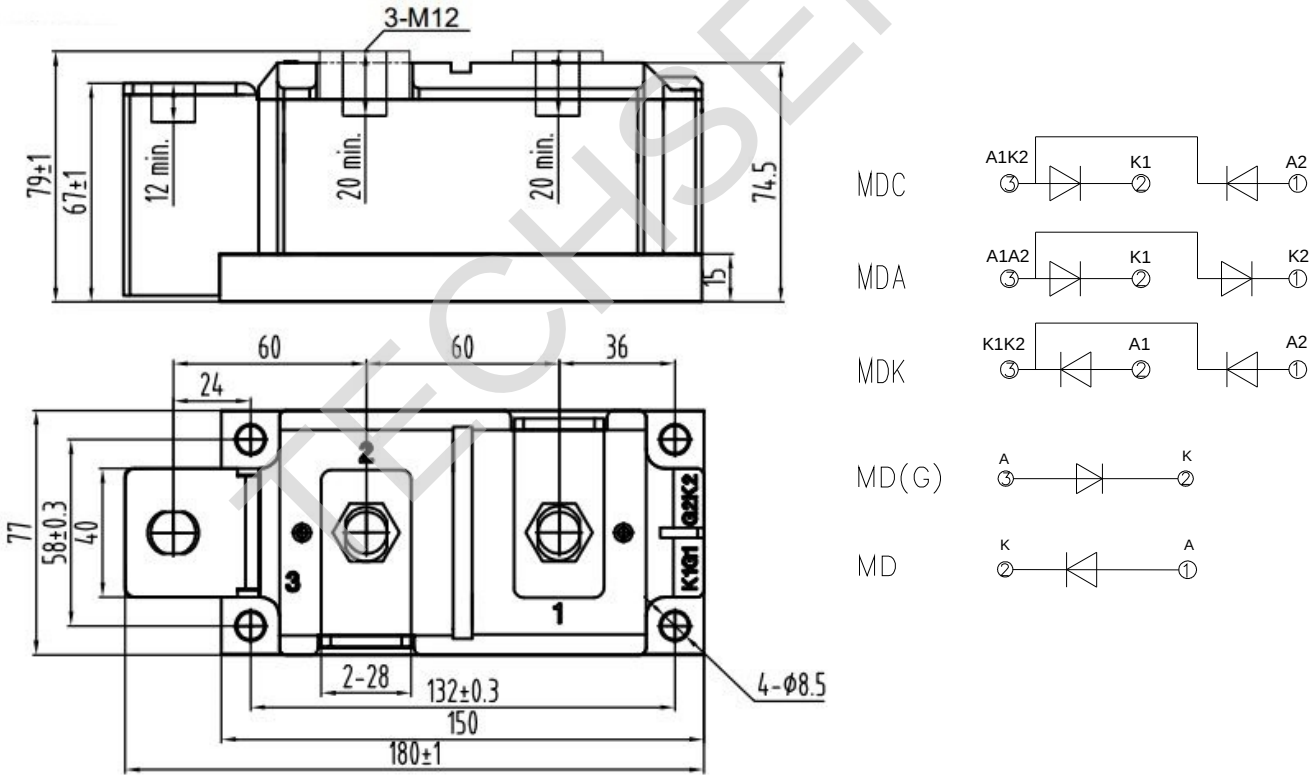
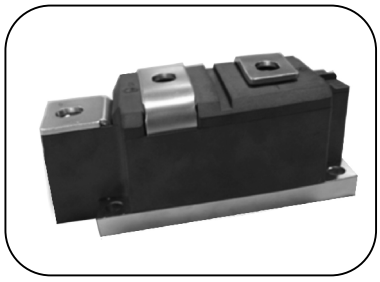


Fig.8

Outline:



Unmarked dimensional tolerance：±0.5mm



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3600V	MD600-36-410F3G

MDx stands for any type of **MDC, MDA, MDK**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			600	A
$I_{F(RMS)}$	RMS forward current					942	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			50	mA
I_{FSM}	Surge forward current	V_R=60%V_{RRM}, t=10ms half sine	150			17.0	kA
I^2t	I^2t for fusing coordination					1445	10^3A^2s
V_{FO}	Threshold voltage		150			0.85	V
r_F	Forward slope resistance					0.40	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1800A	25			1.85	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.054	°C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.024	°C/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(MAX)		4000			V
F_m	Terminal connection torque(M12)			12		16	N·m
	Mounting torque(M8)			10		12	N·m
T_{vj}	Junction temperature			-40		150	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				3310		g
Outline	410F3						

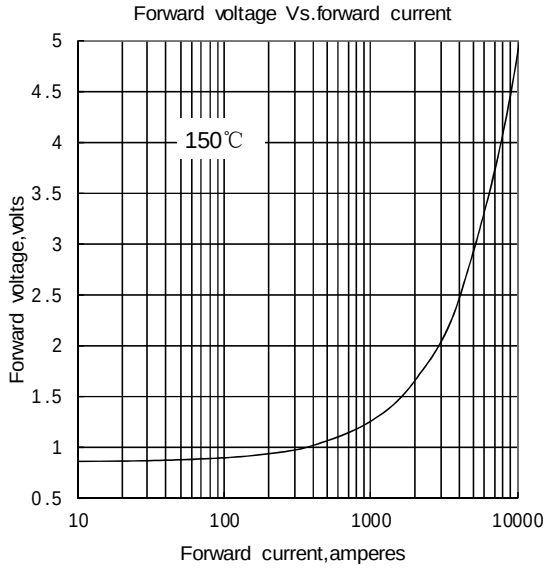


Fig.1

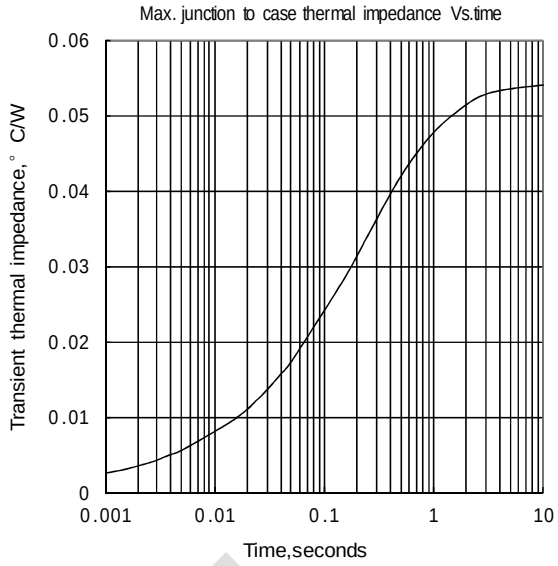


Fig.2

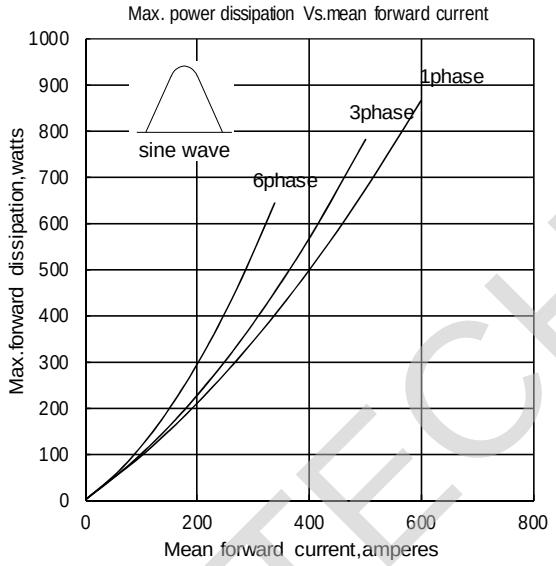


Fig.3

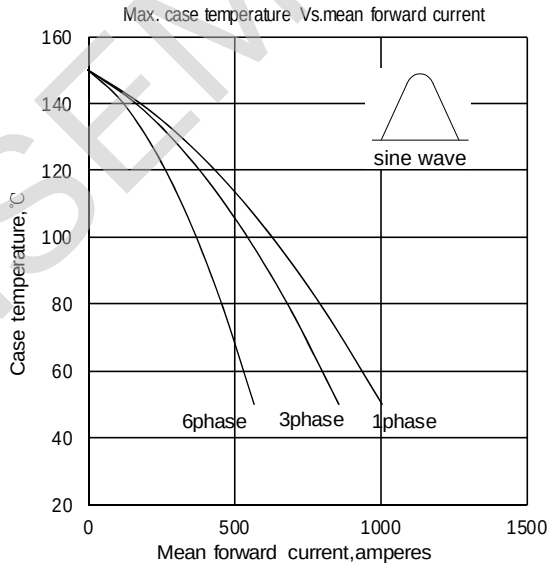


Fig.4

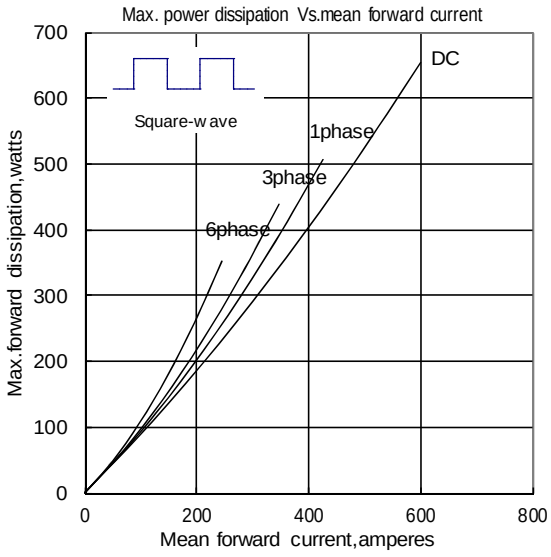


Fig.5

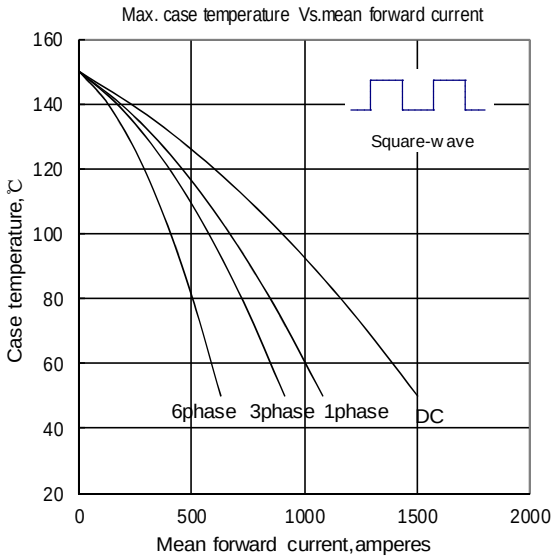


Fig.6

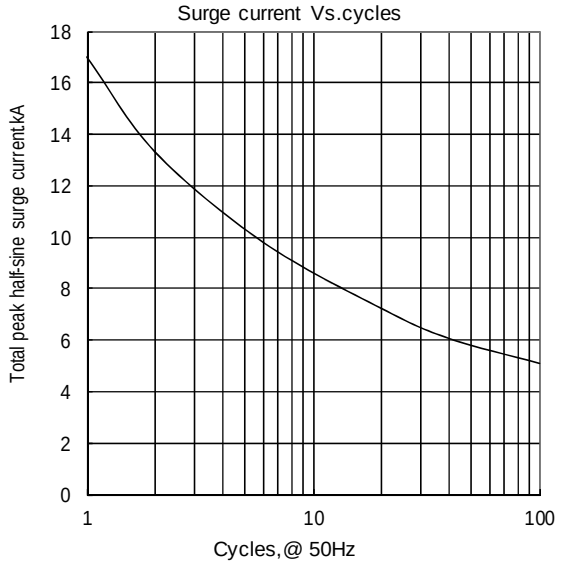


Fig.7

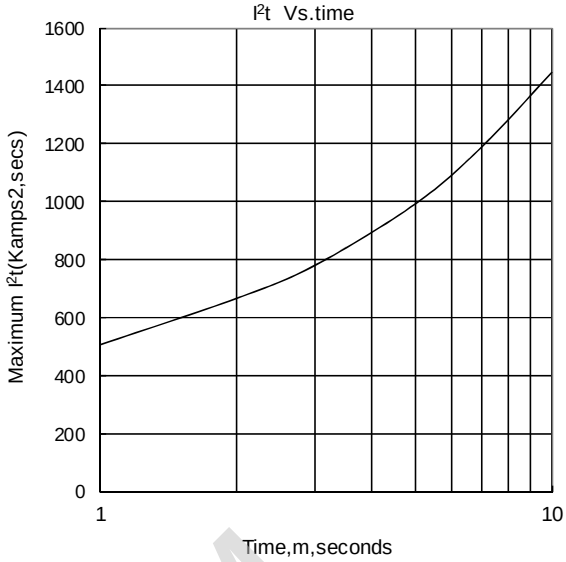
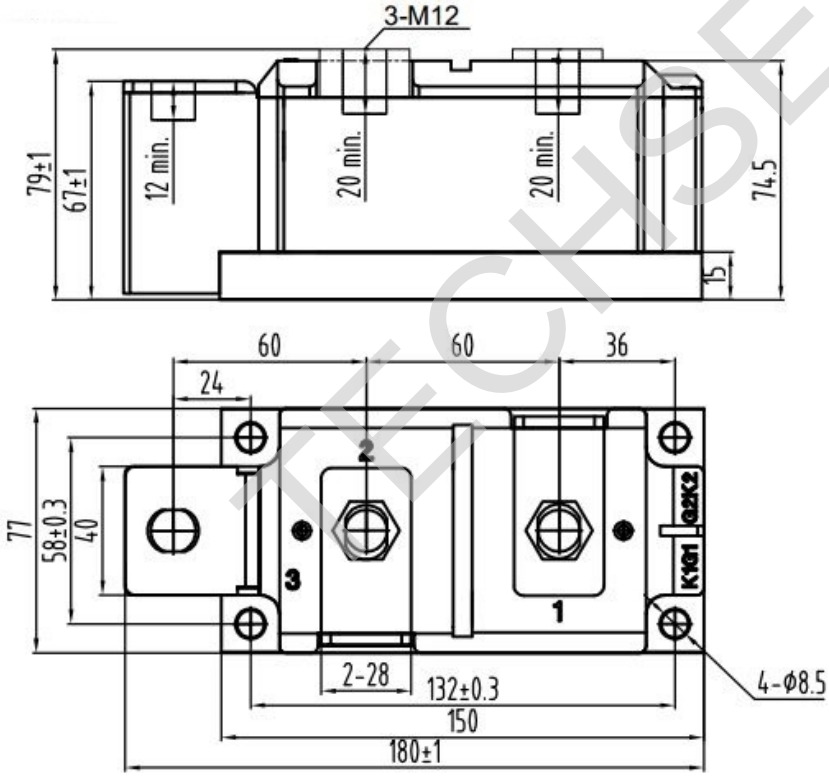
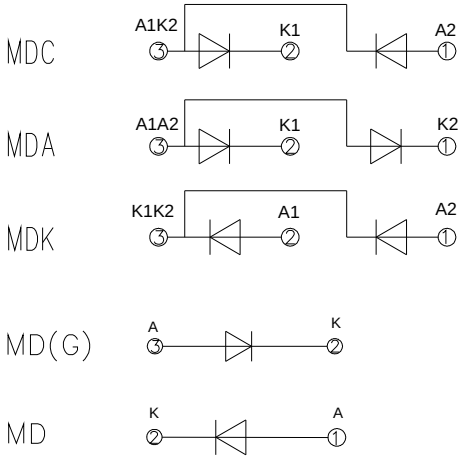


Fig.8

Outline:





Unmarked dimensional tolerance：±0.5mm